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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision E (January 2016) to Revision F	Page
• 已添加特性：与 TPS62090、TLV62095 和 TPS62095 引脚至引脚兼容	1
• 已添加特性：有关改进的功能集，请参见 TPS62090	1
• 已添加 WEBENCH 信息至特性，详细设计流程和器件支持部分	1
• Added SW (AC, less than 10 ns) to the <i>Absolute Maximum Rating</i> table	5
• 已添加 additional frequency curves to the <i>Typical Characteristics</i> section	7
• 已添加 表 1 , Power Good Pin Logic	12

Changes from Revision D (September 2015) to Revision E	Page
• 已将标题由“3A 高效同步”更改至“3A 高效同步”	1
• 已将 特性 “转换器效率为 95%”更改至“效率最高可达 98%”	1
• 已将 特性 “两级短路保护”更改至“断续短路保护”	1
• 已将 说明 中的文本由“该器件在典型值为 20 μ A 的静态电流下工作”更改至“该器件静态工作电流的典型值为 20 μ A。”	1
• Deleted Note from the pinout drawing: <i>The exposed Thermal Pad is connected to AGND.</i>	4
• Changed the <i>Pin Functions</i> table I/O column	4
• Changed the <i>Pin Functions</i> table Description column for pins FB, EN, and Thermal Pad	4
• Added pins CN and CP to the Voltage range in <i>Absolute Maximum Ratings</i> ⁽¹⁾	5
• Deleted "Continuous total power dissipation" from <i>Absolute Maximum Ratings</i> ⁽¹⁾	5
• Deleted Note 1 from <i>Recommended Operating Conditions</i>	5
• Added EN = Low to the Description of R _{PD} in <i>Electrical Characteristics</i> table	6
• Deleted I _{PG} from the <i>Electrical Characteristics</i> table	6
• Changed L _{IMF} to I _{LIMF} for High side FET switch current limit in the <i>Electrical Characteristics</i> table	6
• Changed V _s to V _{OUT} for Output voltage range in the <i>Electrical Characteristics</i> table	6
• Changed 图 1 through 图 2	7
• Added Note 1 to the <i>Functional Block Diagram</i>	9
• Changed "Softstart (SS) and Output Capacitor during Startup" To: Softstart (SS) and Hiccup Current Limit During	

Startup	10
• Changed text From: "start-up especially for larger output capacitors >22 μF." To: "start-up especially for larger output capacitors." in Softstart (SS) and Hiccup Current Limit During Startup	10
• Rewrite the description in Voltage Tracking (SS)	10
• Deleted text "in PFM mode and with a minimum quiescent current while" from Power Save Mode Operation	13
• Changed $V_{OUT(max)}$ to V_{OUT} in 公式 4	13
• Deleted text " $V_{OUT(max)}$ = nominal output voltage plus maximum output voltage tolerance" from 公式 4	13
• Added Note to Application and Implementation	14
• Added 10 nF to the description of C4, C5 in 表 3	15
• Updated the Isat/DCR (max) column of 表 5	16
• Deleted text" The inductor needs to be rated for a saturation current as high as the typical switch current limit, of 4.6 A or according to 公式 5 and 公式 6 ." from Inductor Selection	16
• Changed 公式 5 and 公式 6	16
• Changed the Input and Output Capacitor Selection section	16
• Changed 图 19	18
• Changed 图 20	18

Changes from Revision C (May 2014) to Revision D
Page

• Moved Storage temperature From: ESD Ratings To: Absolute Maximum Ratings ⁽¹⁾	5
• Changed table From: Handling Ratings To: ESD Ratings	5
• Added PWM mode, $T_J = 25^{\circ}C$ to Feedback voltage accuracy section of the Electrical Characteristics table	6

Changes from Revision B (April 2012) to Revision C
Page

• 已添加 ESD 额定值表 , 特性 描述部分 , 器件功能模式 , 应用和实施部分 , 电源相关建议部分 , 布局部分 , 器件和文档支持部分 以及 机械、封装和可订购信息部分 。	1
• Deleted text: "TPS62090 adjustable output version" from the Feedback voltage accuracy section of the Electrical Characteristics table	6
• Changed 图 1 From: Resistance (Ω) To: Resistance ($m\Omega$).....	7
• Added Application Curves to the Application Information section.....	18
• Deleted Typical applications from the Application Information section for: 1.8 V Adjustable Version, 1.5 V Adjustable Version, 1.2 V Adjustable Version and 1.05 V Adjustable Version	20

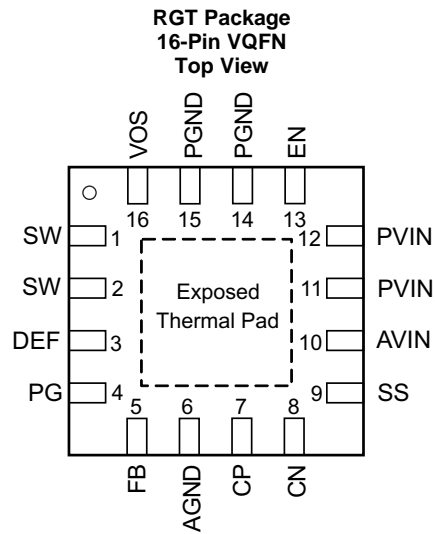
Changes from Revision A (March 2012) to Revision B
Page

• Changed the Input voltage range MAX value From: 6V To 5.5V in Electrical Characteristics	6
--	---

Changes from Original (March 2012) to Revision A
Page

• Changed V_{in} From: 2.5V to 6V To: 2.5V to 5.5V in 图 11	14
--	----

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
SW	1, 2	I/O	Switch pin of the power stage.
DEF	3	I	This pin is used for internal logic and needs to be pulled high. This pin should not be left floating.
PG	4	O	Power good open drain output. This pin is high impedance if the output voltage is within regulation. This pin is pulled low if the output is below its nominal value. The pull up resistor can not be connected to any voltage higher than the input voltage of the device.
FB	5	I	Feedback pin of the device. Connect a resistor divider to set the output voltage.
AGND	6		Analog ground.
CP	7	I/O	Internal charge pump flying capacitor. Connect a 10 nF capacitor between CP and CN.
CN	8	I/O	Internal charge pump flying capacitor. Connect a 10 nF capacitor between CP and CN.
SS	9	I	Softstart control pin. A capacitor is connected to this pin and sets the softstart time. Leaving this pin floating sets the minimum start-up time.
AVIN	10	I	Bias supply input voltage pin.
PVIN	11,12	I	Power supply input voltage pin.
EN	13	I	Device enable. To enable the device this pin needs to be pulled high. Pulling this pin low disables the device. This pin has a pull down resistor of typically 400 k Ω , which is active when EN is low.
PGND	14,15		Power ground connection.
VOS	16	I	Output voltage sense pin. This pin needs to be connected to the output voltage.
Exposed Thermal Pad			The exposed thermal pad is connected to AGND. It must be soldered for mechanical reliability.

6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

		VALUE		UNIT
		MIN	MAX	
Voltage range ⁽²⁾	PVIN, AVIN, FB, SS, EN, DEF, VOS	– 0.3	7	V
	SW (DC), PG	– 0.3	V _{IN} + 0.3	
	SW (AC, less than 10 ns) ⁽³⁾	– 3.0	10	
	CN, CP	– 0.3	V _{IN} + 7	
Power Good sink current	PG		1	mA
Operating junction temperature range, T _J		– 40	150	°C
Storage temperature, T _{stg}		– 65	150	°C

- (1) Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to network ground terminal.
- (3) While switching

6.2 ESD Ratings

			MAX	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

		MIN	TYP	MAX	UNIT
V _{IN}	Input voltage range V _{IN}	2.5		5.5	V
T _A	Operating ambient temperature	–40		85	°C
T _J	Operating junction temperature	–40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TLV62090	UNITS
		VQFN (16 PINS)	
R _{θJA}	Junction-to-ambient thermal resistance	47	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	60	
R _{θJB}	Junction-to-board thermal resistance	20	
Ψ _{JT}	Junction-to-top characterization parameter	1.5	
Ψ _{JB}	Junction-to-board characterization parameter	20	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	5.3	

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

 $V_{IN} = 3.6V$, $T_A = -40^{\circ}C$ to $85^{\circ}C$, typical values are at $T_A = 25^{\circ}C$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY						
V_{IN}	Input voltage range		2.5		5.5	V
I_{QIN}	Quiescent current	Not switching, FB = FB +5%, into PVIN and AVIN		20		μA
I_{sd}	Shutdown current	Into PVIN and AVIN		0.6	5	μA
V_{UVLO}	Undervoltage lockout threshold	V_{IN} falling	2.1	2.2	2.3	V
	Undervoltage lockout hysteresis			200		mV
T_{SD}	Thermal shutdown	Temperature rising		150		$^{\circ}C$
	Thermal shutdown hysteresis			20		$^{\circ}C$
CONTROL SIGNAL EN						
V_H	High level input voltage	$V_{IN} = 2.5 V$ to $5.5 V$	1	0.65		V
V_L	Low level input voltage	$V_{IN} = 2.5 V$ to $5.5 V$		0.60	0.4	V
I_{lkg}	Input leakage current	EN = GND or V_{IN}		10	100	nA
R_{PD}	Pull down resistance	EN = Low		400		k Ω
SOFTSTART						
I_{SS}	Softstart current		6.3	7.5	8.7	μA
POWER GOOD						
V_{TH_PG}	Power good threshold	Output voltage rising	93%	95%	97%	
		Output voltage falling	88%	90%	92%	
V_L	Low level voltage	$I_{(sink)} = 1 mA$			0.4	V
I_{lkg}	Leakage current	$V_{PG} = 3.6 V$		10	100	nA
POWER SWITCH						
$R_{DS(on)}$	High side FET on-resistance	$I_{SW} = 500 mA$		50		m Ω
	Low side FET on-resistance	$I_{SW} = 500 mA$		40		m Ω
I_{LIMF}	High side FET switch current limit		3.7	4.6	5.5	A
f_s	Switching frequency	$I_{OUT} = 3 A$		1.4		MHz
OUTPUT						
V_{OUT}	Output voltage range		0.8		V_{IN}	V
R_{od}	Output discharge resistor	EN = GND, $V_{OUT} = 1.8 V$		200		Ω
V_{FB}	Feedback regulation voltage	PWM Mode		0.8		V
V_{FB}	Feedback voltage accuracy $V_{IN} \geq V_{OUT} + 1 V$	$I_{OUT} = 1 A$, PWM mode, $T_J = 25^{\circ}C$	-1%		+1%	
		$I_{OUT} = 1 A$, PWM mode	-1.4%		+1.4%	
		$I_{OUT} = 0 mA$, $V_{OUT} \geq 1.2 V$, PFM mode ⁽¹⁾	-1.4%		+3%	
		$I_{OUT} = 0 mA$, $V_{OUT} < 1.2 V$, PFM mode ⁽²⁾	-1.4%		+3.7%	
I_{FB}	Feedback input bias current	$V_{FB} = 0.8 V$		10	100	nA
	Line regulation	$V_{OUT} = 1.8 V$, PWM operation		0.016		%/V
	Load regulation	$V_{OUT} = 1.8 V$, PWM operation		0.04		%/A

(1) Conditions: L = 1 μH , $C_{OUT} = 22 \mu F$. For more information, see the [Power Save Mode Operation](#) section of this data sheet.

(2) For output voltages < 1.2 V, use a 2 x 22 μF output capacitance to achieve +3% output voltage accuracy in PFM mode.

6.6 Typical Characteristics

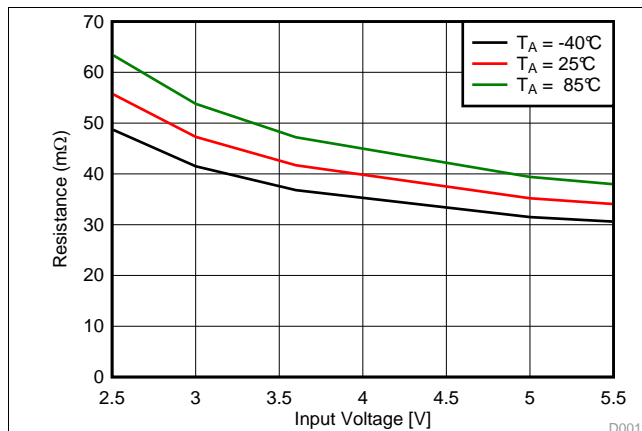


图 1. High Side FET On-Resistance vs Input Voltage

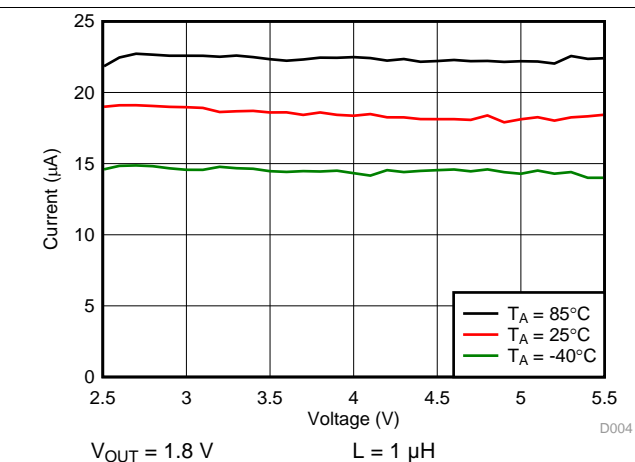


图 2. Quiescent Current vs Input Voltage

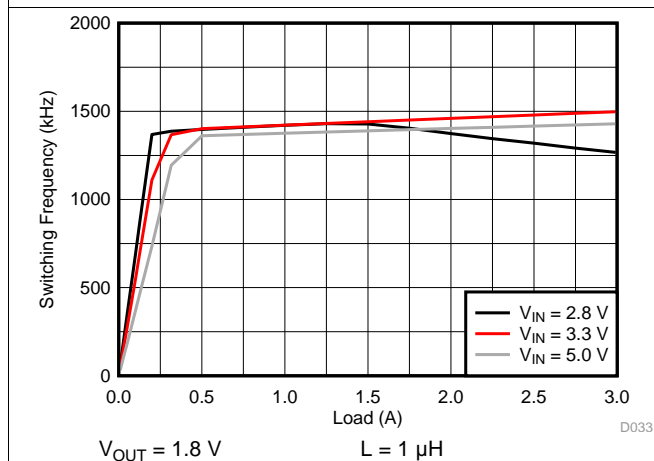


图 3. Switching Frequency vs Load Current

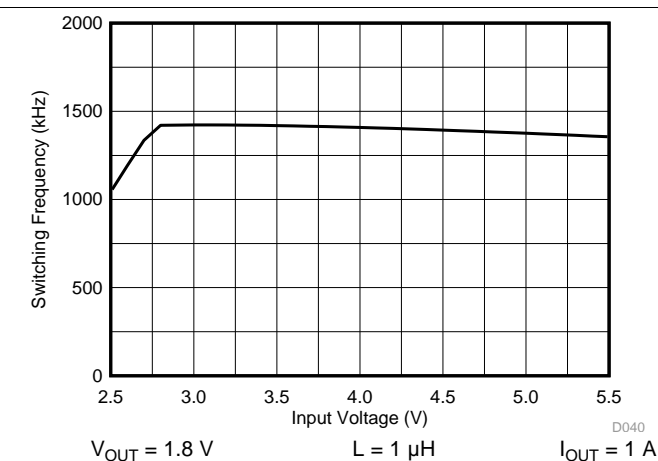


图 4. Switching Frequency vs Input Voltage

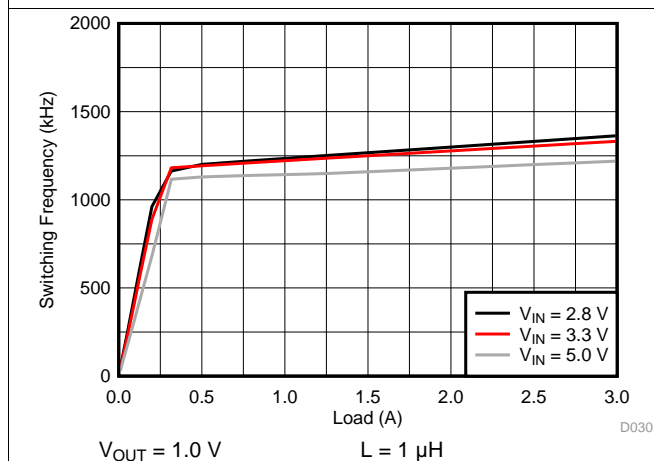


图 5. Switching Frequency vs Load Current

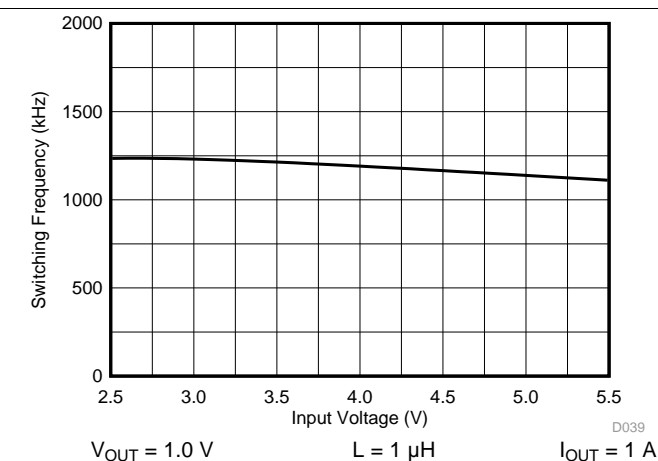
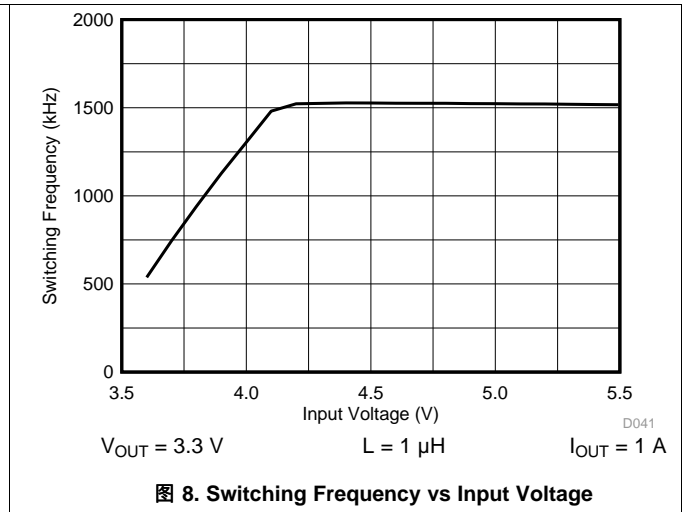
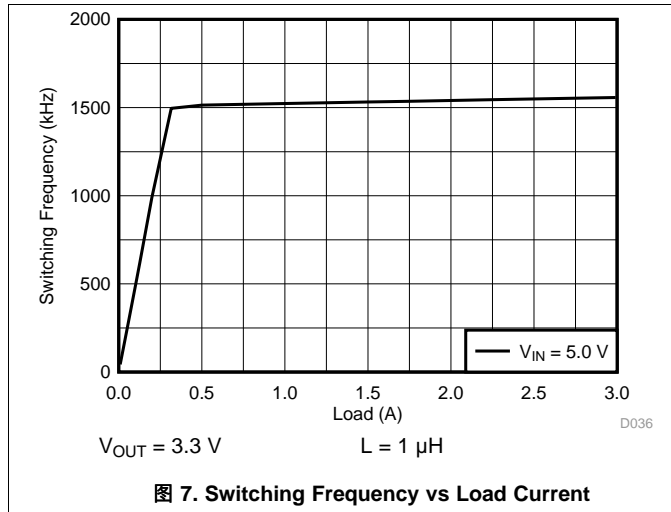


图 6. Switching Frequency vs Input Voltage

Typical Characteristics (接下页)



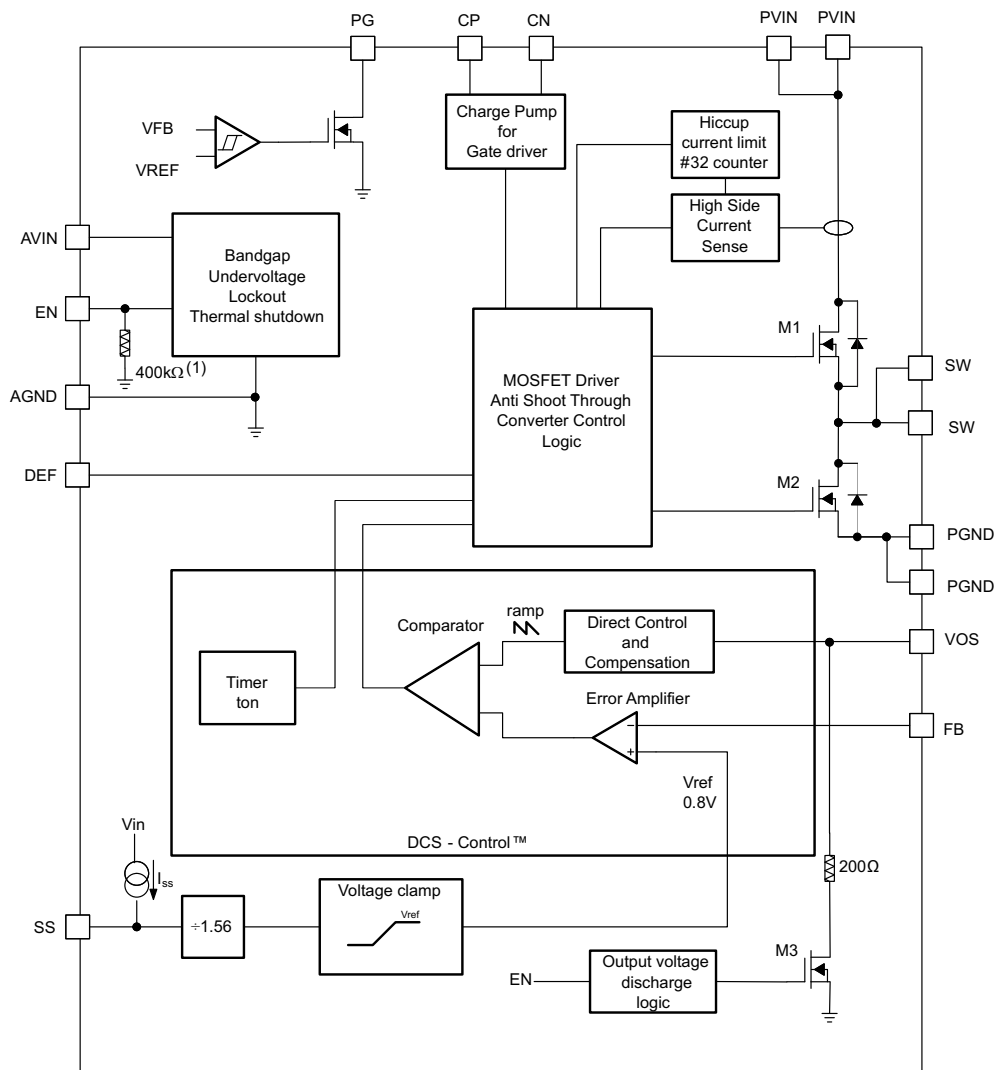
7 Detailed Description

7.1 Overview

The TLV62090 synchronous switched mode converter is based on DCS-Control™ (direct control with seamless transition into power save mode). This is an advanced regulation topology that combines the advantages of hysteretic and voltage-mode control.

The DCS-Control™ topology operates in pulse width modulation (PWM) mode for medium to heavy load conditions and in power save mode at light load currents. In PWM mode, the converter operates with its nominal switching frequency of 1.4 MHz having a controlled frequency variation over the input voltage range. As the load current decreases, the converter enters power save mode, reducing the switching frequency and minimizing the current consumption to achieve high efficiency over the entire load current range. DCS-Control™ supports both operation modes (PWM and PFM) using a single building block having a seamless transition from PWM to power save mode without effects on the output voltage. The TLV62090 offers excellent DC voltage regulation and load transient regulation, combined with low output voltage ripple, minimizing interference with RF circuits.

7.2 Functional Block Diagram



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(1) The resistor is disconnected when EN is high.

7.3 Feature Description

7.3.1 Enable (EN)

The device is enabled by setting the EN pin to a logic high. Accordingly, shutdown mode is forced if the EN pin is pulled low with a shutdown current of typically 0.6 μA . In shutdown mode, the internal power switches as well as the entire control circuitry are turned off. An internal resistor of 200 Ω discharges the output through the VOS pin smoothly. An internal pull-down resistor of 400 k Ω is connected to the EN pin when the EN pin is low. The pull-down resistor is disconnected when the EN pin is high.

7.3.2 Softstart (SS) and Hiccup Current Limit During Startup

To minimize inrush current during start up, the device has an adjustable softstart depending on the capacitor value connected to the SS pin. The device charges the softstart capacitor with a constant current of typically 7.5 μA . The feedback voltage follows this voltage with a fraction of 1.56 until the internal reference voltage of 0.8 V is reached. Softstart operation is completed once the voltage at the softstart capacitor has reached typically 1.25 V. The softstart time is calculated using [公式 1](#). The larger the softstart capacitor, the longer the softstart time. The relation between softstart voltage and feedback voltage is estimated using [公式 2](#).

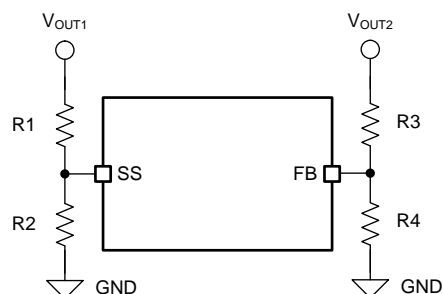
$$t_{\text{SS}} = C_{\text{SS}} \times \frac{1.25\text{V}}{7.5\mu\text{A}} \quad (1)$$

$$V_{\text{FB}} = \frac{V_{\text{SS}}}{1.56} \quad (2)$$

During startup, the switch current limit is reduced to 1/3 (~1.5 A) of its typical current limit of 4.6 A. Once the output voltage exceeds typically 0.6 V, the current limit is released to its nominal value. The device provides a reduced load current of ~1.5 A when the output voltage is below typically 0.6 V. Due to this, a small or no softstart time may trigger the short circuit protection during startup especially for larger output capacitors. This is avoided by using a larger softstart capacitance to extend the softstart time. See [Short Circuit Protection \(Hiccup-Mode\)](#) for details of the reduced current limit during startup. Leaving the softstart pin floating sets the minimum startup time (around 50 μs).

7.3.3 Voltage Tracking (SS)

The SS pin is externally driven by another voltage source to achieve output voltage tracking. The application circuit is shown in [图 9](#). The internal reference voltage follows the voltage at the SS pin with a fraction of 1.56 until the internal reference voltage of 0.8 V is reached. The device achieves ratiometric or coincidental (simultaneous) output tracking, as shown in [图 10](#).



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图 9. Output Voltage Tracking

Feature Description (接下页)

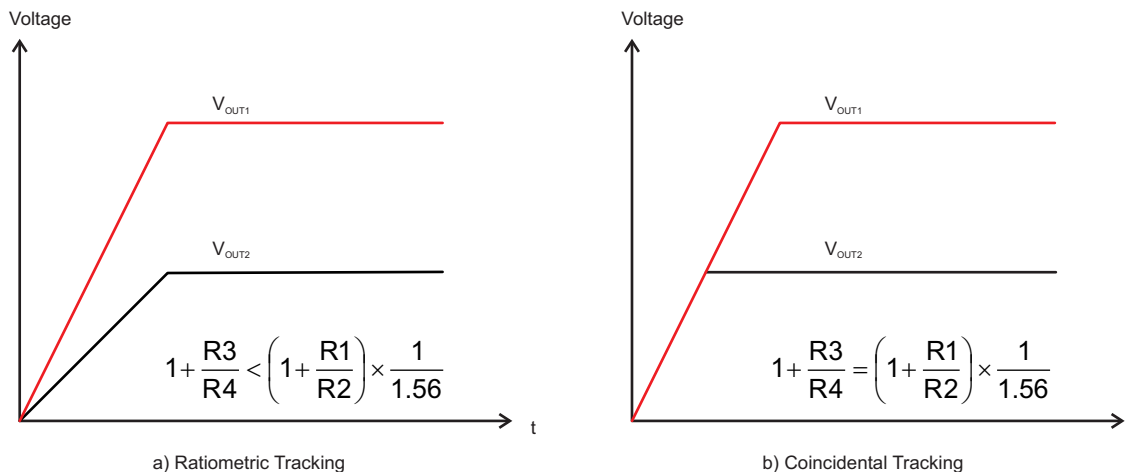


图 10. Voltage Tracking Options

The R2 value should be set properly to achieve accurate voltage tracking by taking 7.5 μA soft startup current into account. 1 kΩ or smaller is a sufficient value for R2.

For decreasing the SS pin voltage, the device doesn't sink current from the output when the device is in power save mode. So the resulting decreases of the output voltage may be slower than the SS pin voltage if the load is light. When driving the SS pin with an external voltage, do not exceed the voltage rating of the SS pin which is 7 V.

7.3.4 Short Circuit Protection (Hiccup-Mode)

The device is protected against hard short circuits to GND and over-current events. This is implemented by a two level short circuit protection. During startup and when the output is shorted to GND, the switch current limit is reduced to 1/3 of its typical current limit of 4.6 A. Once the output voltage exceeds typically 0.6 V, the current limit is released to its nominal value. The full current limit is implemented as a hiccup current limit. Once the internal current limit is triggered 32 times, the device stops switching and starts a new startup sequence after a typical delay time of 66 μS. The device goes through these cycles until the high current condition is released.

7.3.5 Output Discharge Function

To make sure the device starts up under defined conditions, the output gets discharged via the VOS pin with a typical discharge resistor of 200 Ω whenever the device shuts down. This happens when the device is disabled or if thermal shutdown, undervoltage lockout or short circuit hiccup-mode are triggered.

Feature Description (接下页)

7.3.6 Power Good Output (PG)

The power good output is low when the output voltage is below its nominal value. The power good becomes high impedance once the output is within 5% of regulation. The PG pin is an open drain output and is specified to typically sink up to 1 mA. This output requires a pull-up resistor to be monitored properly. The pull-up resistor cannot be connected to any voltage higher than the input voltage of the device. The PG output is low when the device is disabled, in thermal shutdown or UVLO. The PG output can be left floating if unused. 表 1 shows the PG pin logic.

表 1. Power Good Pin Logic

Device State		PG Logic Status	
		High Impedance	Low
Enable (EN=High)	$V_{FB} \geq V_{TH_PG}$	√	
	$V_{FB} \leq V_{TH_PG}$		√
Shutdown (EN=Low)			√
UVLO	$0.7\text{ V} < V_{IN} \leq V_{UVLO}$		√
Thermal Shutdown	$T_J > T_{SD}$		√
Power Supply Removal	$V_{IN} \leq 0.7\text{ V}$	√	

7.3.7 Undervoltage Lockout (UVLO)

To avoid mis-operation of the device at low input voltages, an undervoltage lockout is included. UVLO shuts down the device at input voltages lower than typically 2.2 V with a 200 mV hysteresis.

7.3.8 Thermal Shutdown

The device goes into thermal shutdown once the junction temperature exceeds typically 150°C with a 20°C hysteresis.

7.3.9 Charge Pump (CP, CN)

The CP and CN pins must attach to an external 10 nF capacitor to complete a charge pump for the gate driver. This capacitor must be rated for the input voltage. It is not recommended to connect any other circuits to the CP or CN pins.

7.4 Device Functional Modes

7.4.1 PWM Operation

At medium to heavy load currents, the device operates with pulse width modulation (PWM) at a nominal switching frequency of 1.4 MHz. As the load current decreases, the converter enters power save mode operation reducing its switching frequency. The device enters power save mode at the boundary to discontinuous conduction mode (DCM).

7.4.2 Power Save Mode Operation

As the load current decreases, the converter enters power save mode operation. During power save mode, the converter operates with reduced switching frequency maintaining high efficiency. Power save mode is based on a fixed on-time architecture following [公式 3](#).

$$\begin{aligned}
 t_{on} &= \frac{V_{OUT}}{V_{IN}} \times 360\text{ns} \times 2 \\
 f &= \frac{2 \times I_{OUT}}{t_{on}^2 \left(1 + \frac{V_{IN} - V_{OUT}}{V_{OUT}} \right) \times \frac{V_{IN} - V_{OUT}}{L}}
 \end{aligned}
 \tag{3}$$

In power save mode, the output voltage rises slightly above the nominal output voltage in PWM mode, as shown in [图 15](#). This effect is reduced by increasing the output capacitance or the inductor value. This effect is also reduced by programming the output voltage of the TLV62090 lower than the target value. As an example, if the target output voltage is 3.3 V, then the TLV62090 can be programmed to 3.3 V - 0.8%. As a result the output voltage accuracy is now -2.2% to +2.2% instead of -1.4% to 3%. The output voltage accuracy in pulse frequency modulation (PFM) operation is reflected in the electrical specification table and given for a 22-μF output capacitor.

7.4.3 Low Dropout Operation (100% Duty Cycle)

The device offers a low input to output voltage difference by entering 100% duty cycle mode. In this mode, the high-side MOSFET switch is constantly turned on. This is particularly useful in battery powered applications to achieve longest operation time by taking full advantage of the whole battery voltage range. The minimum input voltage where the output voltage falls below its nominal regulation value is given by:

$$V_{IN(\min)} = V_{OUT} + I_{OUT} \times (R_{DS(on)} + R_L)
 \tag{4}$$

Where

$R_{DS(on)}$ = High side FET on-resistance

R_L = DC resistance of the inductor

8 Application and Implementation

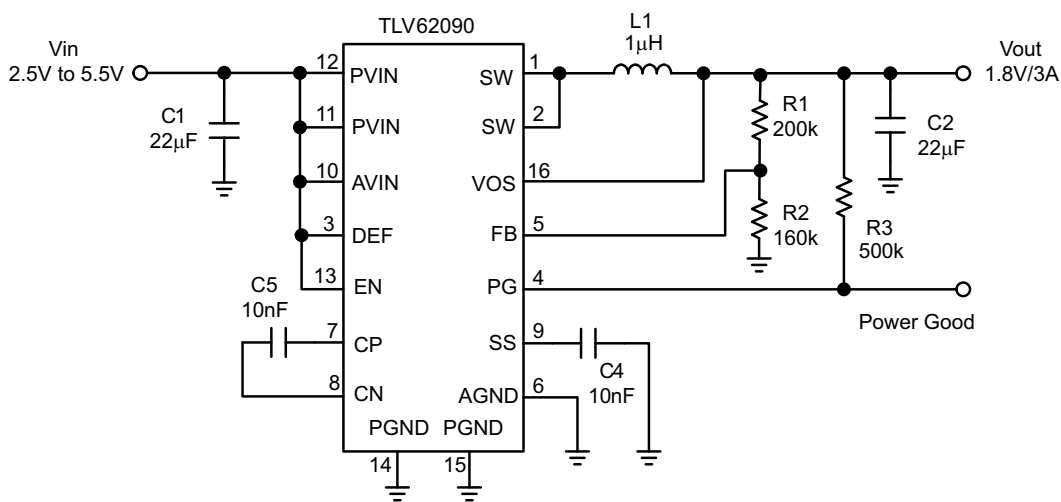
注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TLV62090 is a 3-A high frequency synchronous step-down converter optimized for small solution size, high efficiency and suitable for battery powered applications.

8.2 Typical Application



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图 11. TLV62090 Typical Application Circuit

8.2.1 Design Requirements

The design guideline provides a component selection to operate the device within the recommended operating conditions.

For the typical application example, the following input parameters are used. See 表 2.

表 2. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUES
Input Voltage Range	2.5 V to 5.5 V
Output Voltage	1.8 V
Transient Response	±5% VOUT
Input Voltage Ripple	400 mV
Output Voltage Ripple	30 mV
Output current rating	3 A
Operating frequency	1.4 MHz

表 3 shows the list of components for the Application Characteristic Curves.

表 3. List of Components

REFERENCE	DESCRIPTION	MANUFACTURER
TLV62090	High efficiency step-down converter	Texas Instruments
L1	Inductor: 1 μ H	Coilcraft XFL4020-102
C1	Ceramic capacitor: 22 μ F	(6.3V, X5R, 0805)
C2	Ceramic capacitor: 22 μ F	(6.3V, X5R, 0805)
C4, C5	Ceramic capacitor, 10 nF	Standard
R1, R2, R3	Resistor	Standard

8.2.2 Detailed Design Procedure

8.2.2.1 Custom Design with WEBENCH® Tools

[Click here](#) to create a custom design using the TLV62090 device with the WEBENCH® Power Designer.

1. Start by entering your V_{IN} , V_{OUT} , and I_{OUT} requirements.
2. Optimize your design for key parameters like efficiency, footprint and cost using the optimizer dial and compare this design with other possible solutions from Texas Instruments.
3. The WEBENCH Power Designer provides you with a customized schematic along with a list of materials with real time pricing and component availability.
4. In most cases, you will also be able to:
 - Run electrical simulations to see important waveforms and circuit performance
 - Run thermal simulations to understand the thermal performance of your board
 - Export your customized schematic and layout into popular CAD formats
 - Print PDF reports for the design, and share your design with colleagues
5. Get more information about WEBENCH tools at www.ti.com/WBENCH.

The first step is the selection of the output filter components. To simplify this process, [表 4](#) outlines possible inductor and capacitor value combinations.

表 4. Output Filter Selection

INDUCTOR VALUE [μ H] ⁽¹⁾	OUTPUT CAPACITOR VALUE [μ F] ⁽²⁾				
	10	22	47	100	150
0.47		√	√	√	√
1.0	√	√ ⁽³⁾	√	√	√
2.2	√	√	√	√	√
3.3					

- (1) Inductor tolerance and current de-rating is anticipated. The effective inductance can vary by +20% and –30%.
- (2) Capacitance tolerance and bias voltage de-rating is anticipated. The effective capacitance can vary by +20% and –50%.
- (3) Typical application configuration. Other check mark indicates alternative filter combinations

8.2.2.2 Inductor Selection

The inductor selection is affected by several parameters like inductor ripple current, output voltage ripple, transition point into power save mode, and efficiency. See 表 5 for typical inductors.

表 5. Inductor Selection

INDUCTOR VALUE	COMPONENT SUPPLIER	SIZE (LxWxH mm)	Isat/DCR (max)
0.6 μH	Coilcraft XAL4012-601	4 x 4 x 2.1	7.9A/10.5 mΩ
1 μH	Coilcraft XAL4020-102	4 x 4 x 2.1	6.7A/14.6 mΩ
1 μH	Coilcraft XFL4020-102	4 x 4 x 2.1	4.5 A/11.9 mΩ
0.47 μH	TOKO DFE252012CR47	2.5 x 2 x 1.2	3.7A/39 mΩ
1 μH	TOKO DFE252012C1R0	2.5 x 2 x 1.2	3.0A/59 mΩ
0.68 μH	TOKO DFE322512CR68	3.2 x 2.5 x 1.2	3.5A/35 mΩ
1 μH	TOKO DFE322512C1R0	3.2 x 2.5 x 1.2	3.1A/45 mΩ

In addition, the inductor has to be rated for the appropriate saturation current and DC resistance (DCR). 公式 5 and 公式 6 calculate the maximum inductor current under static load conditions. The formula takes the converter efficiency into account. The converter efficiency can be taken from the data sheet graphs or 80% can be used as a conservative approach. The calculation must be done for the maximum input voltage where the peak switch current is highest.

$$\Delta I_L = \frac{V_{OUT}}{\eta} \times \left(1 - \frac{V_{OUT}}{V_{IN} \times \eta} \right) \div (f \times L) \quad (5)$$

$$I_{PEAK} = I_{OUT} + \frac{\Delta I_L}{2} \quad (6)$$

where

f = Converter switching frequency (typically 1.4 MHz)

L = Selected inductor value

η = Estimated converter efficiency (use the number from the efficiency curves or 0.80 as a conservative assumption)

Calculating the maximum inductor current using the actual operating conditions gives the minimum saturation current. A margin of about 20% should be added to cover for load transients during operation.

8.2.2.3 Input and Output Capacitor Selection

For best output and input voltage filtering, low ESR (X5R or X7R) ceramic capacitors are recommended. The input capacitor minimizes input voltage ripple, suppresses input voltage spikes and provides a stable system rail for the device. A 22-μF or larger input capacitor is recommended. The output capacitor value can range from 10 μF up to 150 μF and beyond. Load transient testing and measuring the bode plot are good ways to verify stability with larger capacitor values.

The recommended typical output capacitor value is 22 μF (nominal) and can vary over a wide range as outline in the output filter selection table. For output voltages above 1.8 V, noise can cause duty cycle jitter. This does not degrade device performance. Using an output capacitor of 2 x 22 μF (nominal) for output voltages >1.8 V avoids duty cycle jitter.

Ceramic capacitor have a DC-Bias effect, which has a strong influence on the final effective capacitance. Choose the right capacitor carefully in combination with considering its package size and voltage rating.

8.2.2.4 Setting the Output Voltage

The output voltage is set by an external resistor divider according to the following equations:

$$V_{OUT} = V_{FB} \times \left(1 + \frac{R1}{R2}\right) = 0.8 \text{ V} \times \left(1 + \frac{R1}{R2}\right) \quad (7)$$

$$R2 = \frac{V_{FB}}{I_{FB}} = \frac{0.8 \text{ V}}{5 \mu\text{A}} \approx 160 \text{ k}\Omega \quad (8)$$

$$R1 = R2 \times \left(\frac{V_{OUT}}{V_{FB}} - 1\right) = R2 \times \left(\frac{V_{OUT}}{0.8\text{V}} - 1\right) \quad (9)$$

When sizing R2, in order to achieve low quiescent current and acceptable noise sensitivity, use a minimum of 5 μA for the feedback current I_{FB} . Larger currents through R2 improve noise sensitivity and output voltage accuracy. A feed forward capacitor is not required for proper operation.

8.2.3 Application Curves

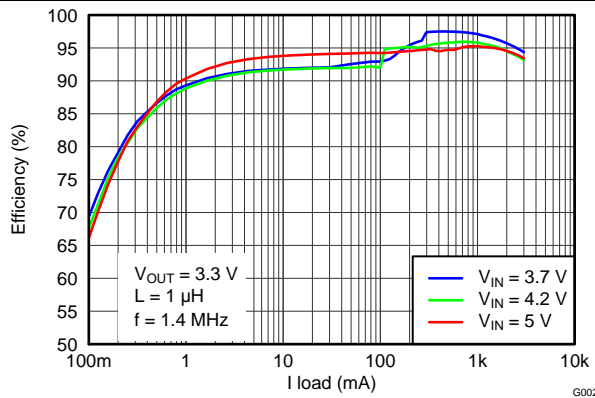


图 12. Efficiency vs Load Current

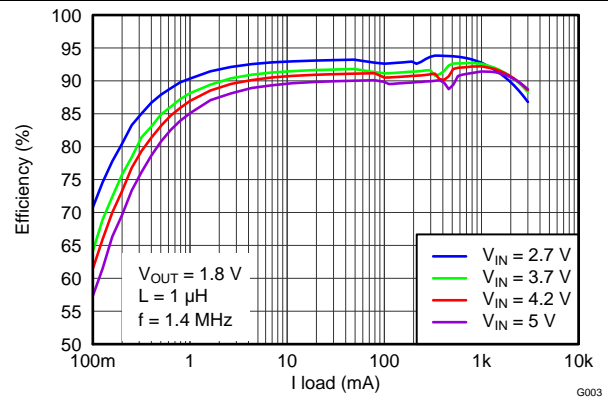


图 13. Efficiency vs Load Current

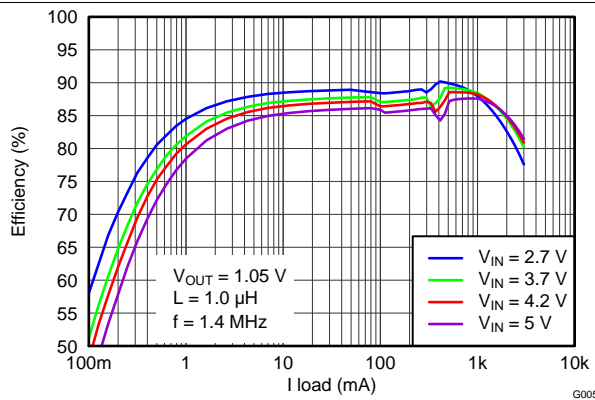


图 14. Efficiency vs Load Current

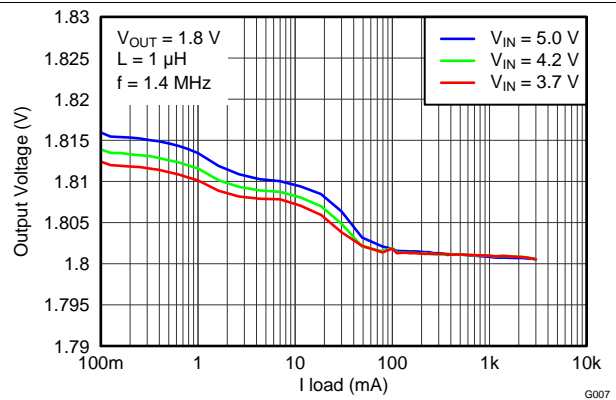


图 15. Output Voltage vs Load Current

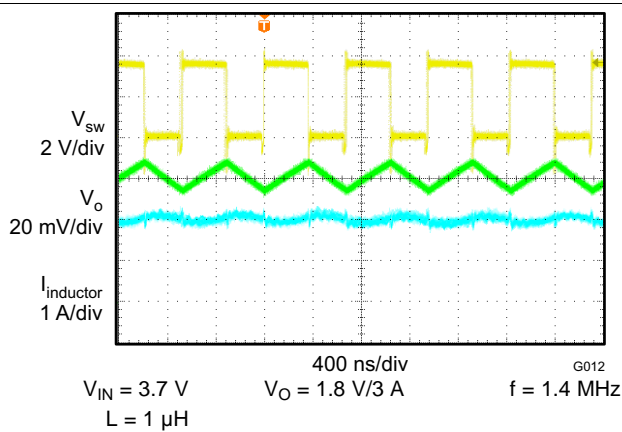


图 16. PWM Operation

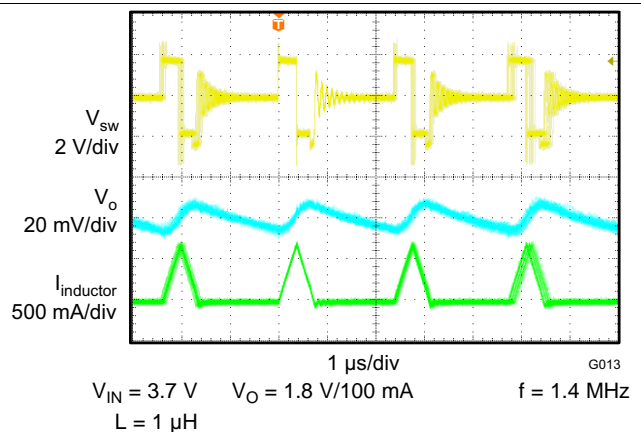


图 17. PFM Operation

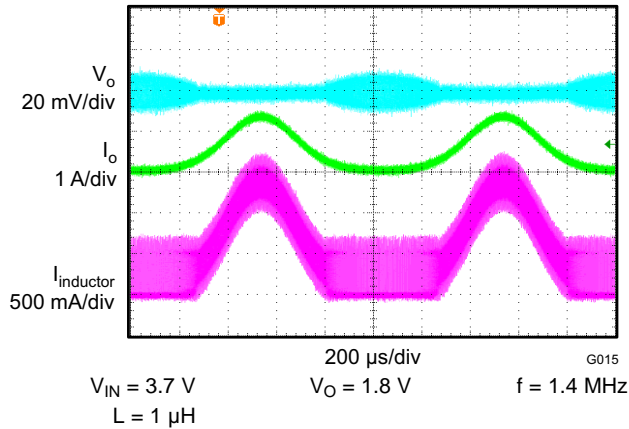


图 18. Load Sweep, 0 to 1.5 A

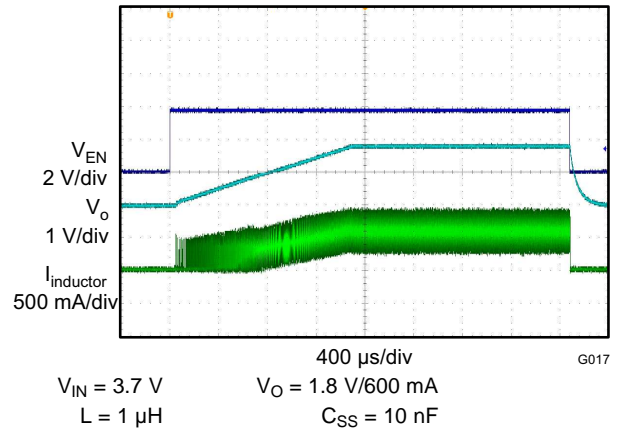


图 19. Start-Up

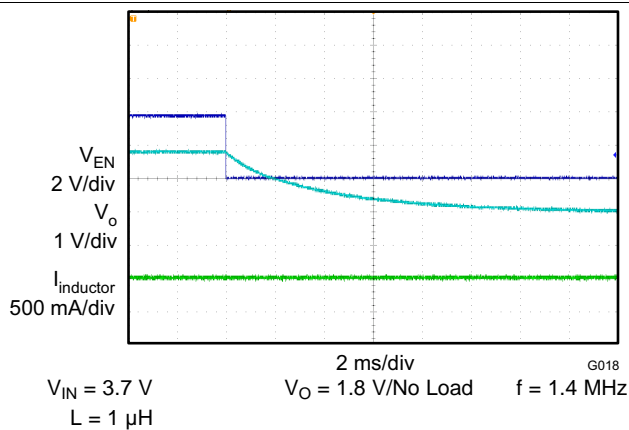


图 20. Shutdown

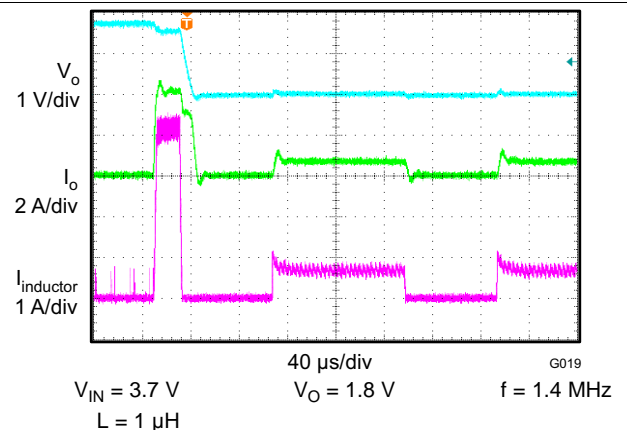


图 21. Hiccup Short Circuit Protection

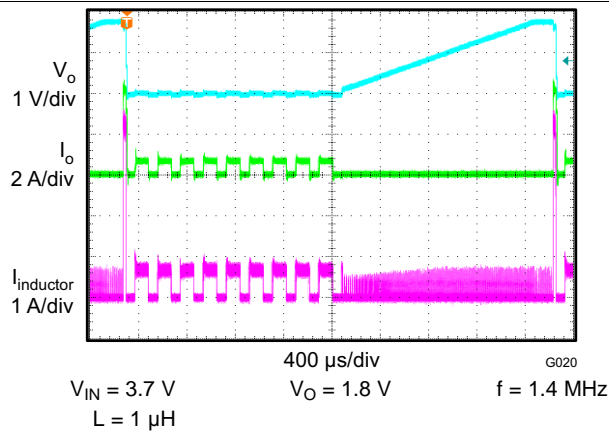


图 22. Hiccup Short Circuit Protection

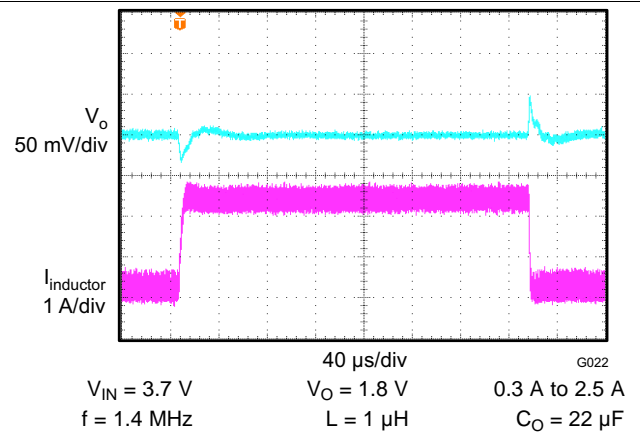


图 23. Load Transient Response

10 Layout

10.1 Layout Guideline

- It is recommended to place the input capacitor as close as possible to the IC pins PVIN and PGND.
- The VOS connection is noise sensitive and needs to be routed short and direct to the output terminal of the inductor.
- The exposed thermal pad of the package, analog ground (pin 6) and power ground (pin 14, 15) should have a single point connection at the exposed thermal pad of the package. This minimizes switch node jitter.
- The charge pump capacitor connected to CP and CN should be placed close to the IC to minimize coupling of switching waveforms into other traces and circuits.
- See [图 25](#) and the evaluation module User Guide (SLVU670) for an example of component placement, routing and thermal design.

10.2 Layout Example

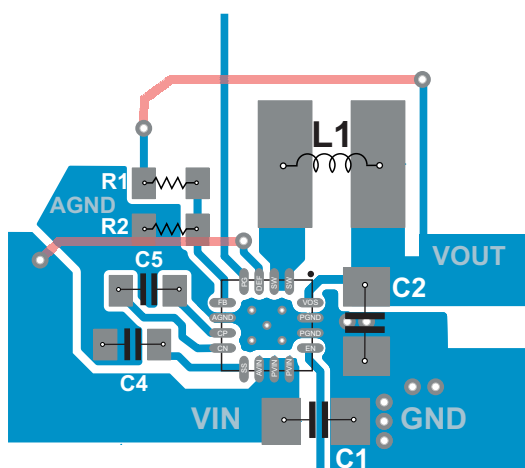


图 25. Recommended Layout

11 器件和文档支持

11.1 器件支持

11.1.1 使用 WEBENCH® 工具定制设计方案

请单击[此处](#)，借助 并使用 TLV62090 器件定制设计方案 WEBENCH®Power Designer 并使用 TLV62090 器件定制设计方案。

1. 首先输入您的 V_{IN} 、 V_{OUT} 和 I_{OUT} 要求。
2. 使用优化器拨盘可优化效率、封装和成本等关键设计参数并将您的设计与德州仪器 (TI) 的其他可行解决方案进行比较。
3. WEBENCH Power Designer 提供一份定制原理图以及罗列实时价格和组件可用性的物料清单。
4. 在多数情况下，您还可以：
 - 运行电气仿真，观察重要波形以及电路性能
 - 运行热性能仿真，了解电路板热性能
 - 将定制原理图和布局方案导出至常用 CAD 格式
 - 打印设计方案的 PDF 报告并与同事共享
5. 有关 WEBENCH 工具的详细信息，请访问 www.ti.com/WEBENCH。

11.2 文档支持

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Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

11.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

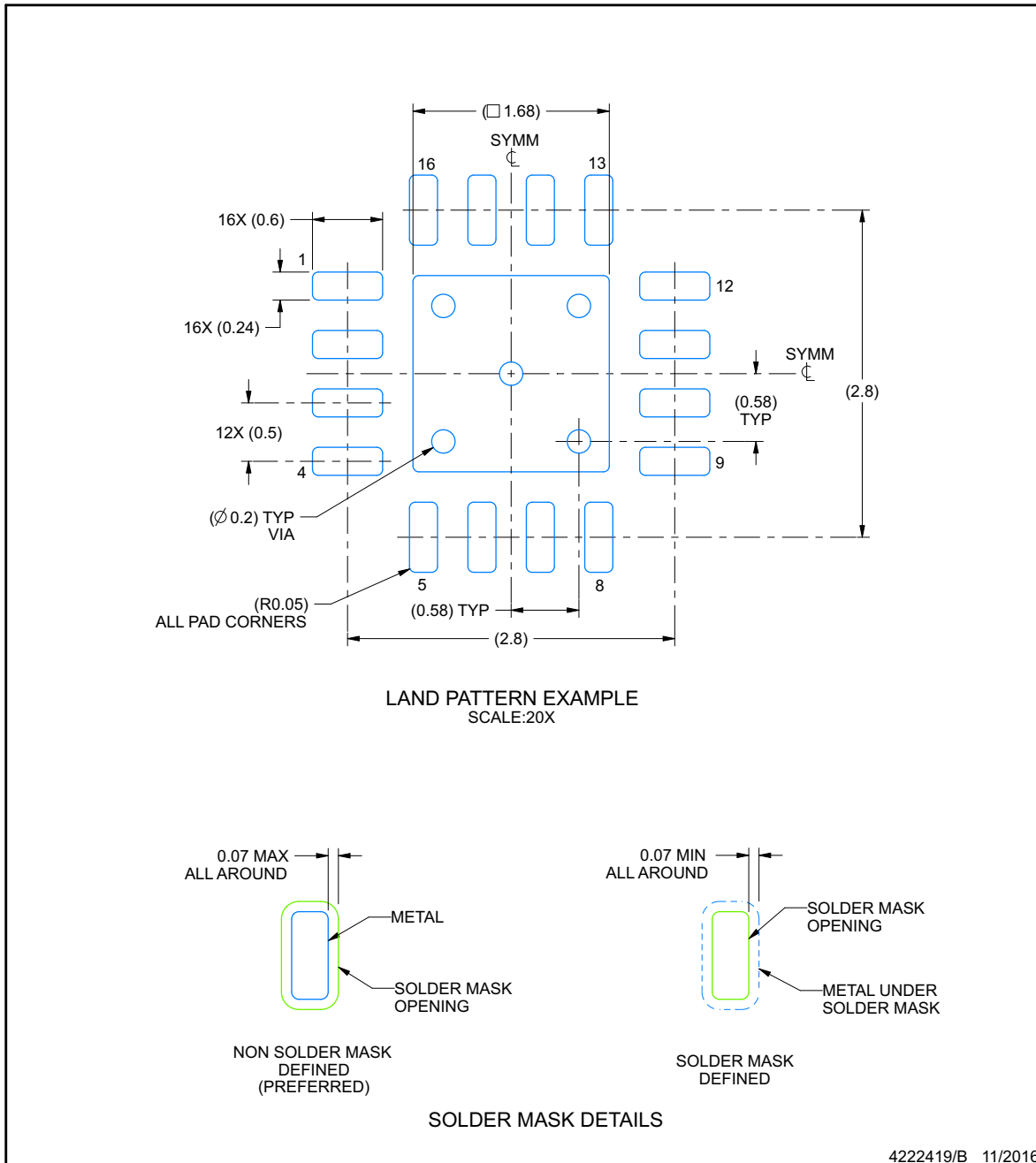
以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

EXAMPLE BOARD LAYOUT

RGT0016C

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

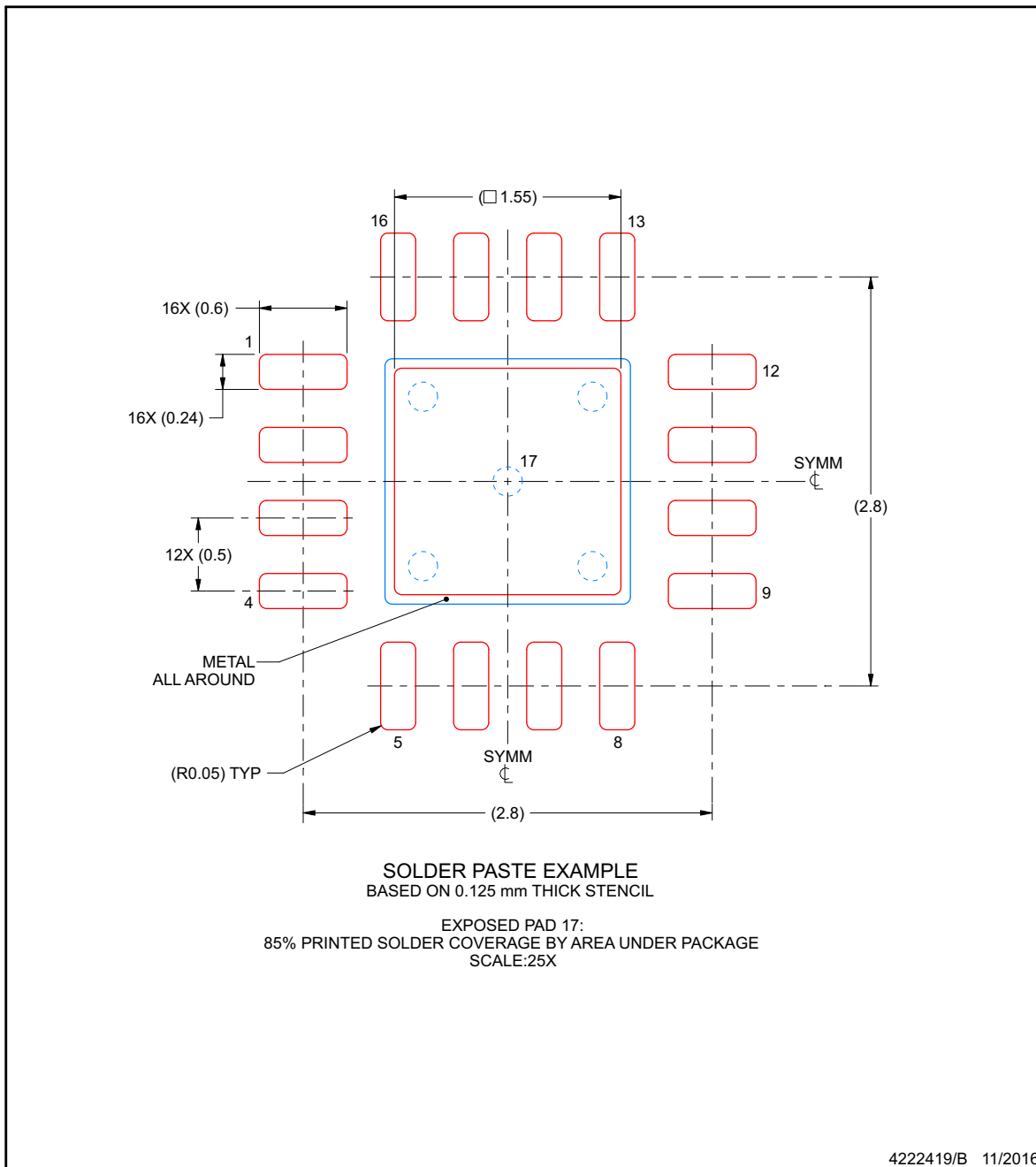
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RGT0016C

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TLV62090RGTR	Active	Production	VQFN (RGT) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SBV
TLV62090RGTR.A	Active	Production	VQFN (RGT) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SBV
TLV62090RGTR.B	Active	Production	VQFN (RGT) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SBV
TLV62090RGTRG4	Active	Production	VQFN (RGT) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SBV
TLV62090RGTRG4.A	Active	Production	VQFN (RGT) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SBV
TLV62090RGTRG4.B	Active	Production	VQFN (RGT) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SBV
TLV62090RGTT	Active	Production	VQFN (RGT) 16	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SBV
TLV62090RGTT.A	Active	Production	VQFN (RGT) 16	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SBV
TLV62090RGTT.B	Active	Production	VQFN (RGT) 16	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SBV

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

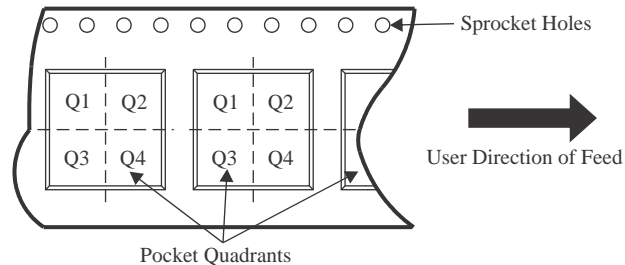
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV62090RGTR	VQFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV62090RGTR	VQFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV62090RGTR	VQFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV62090RGTRG4	VQFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV62090RGTT	VQFN	RGT	16	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV62090RGTT	VQFN	RGT	16	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV62090RGTR	VQFN	RGT	16	3000	367.0	367.0	35.0
TLV62090RGTR	VQFN	RGT	16	3000	346.0	346.0	33.0
TLV62090RGTR	VQFN	RGT	16	3000	338.0	355.0	35.0
TLV62090RGTRG4	VQFN	RGT	16	3000	346.0	346.0	33.0
TLV62090RGTT	VQFN	RGT	16	250	210.0	185.0	35.0
TLV62090RGTT	VQFN	RGT	16	250	210.0	185.0	35.0

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最后更新日期：2025 年 10 月